

# **MPSA44G Datasheet**



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DiGi Electronics Part Number

MPSA44G-DG

Manufacturer

onsemi

Manufacturer Product Number

MPSA44G

Description

TRANS NPN 400V 0.3A TO92

**Detailed Description** 

Bipolar (BJT) Transistor NPN 400 V 300 mA 625 mW

Through Hole TO-92 (TO-226)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MPSA44G	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	300 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
400 V	750mV @ 5mA, 50mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
500nA	50 @ 10mA, 10V
Power - Max:	Frequency - Transition:
625 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 Long Body	TO-92 (TO-226)
Base Product Number:	
MPSA44	

# **Environmental & Export classification**

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 21 0095

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**Preferred Device** 

# **High Voltage Transistor**

# **NPN Silicon**

### **Features**

• Pb-Free Packages are Available\*

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	400	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	500	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current – Continuous	Ic	300	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS

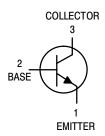
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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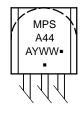
http://onsemi.com



#### MARKING DIAGRAM



TO-92 (TO-226AA) CASE 29-11 STYLE 1



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<b>-</b>	1		
Collector – Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	400	_	Vdc
Collector – Emitter Breakdown Voltage ( $I_C = 100 \mu Adc, V_{BE} = 0$ )	V <sub>(BR)</sub> CES	500	_	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	V <sub>(BR)CBO</sub>	500	_	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc$ , $I_C = 0$ )	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 400 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	0.1	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 400 Vdc, V <sub>BE</sub> = 0)	I <sub>CES</sub>	_	500	nAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	0.1	μAdc
ON CHARACTERISTICS (Note 1)		•		•
DC Current Gain (Note 1) $ \begin{aligned} &(I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=50 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ &(I_C=100 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \end{aligned} $	h <sub>FE</sub>	40 50 45 40	_ 200 _ _	-
Collector – Emitter Saturation Voltage (Note 1) ( $I_C = 1.0 \text{ mAdc}$ , $I_B = 0.1 \text{ mAdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	- - -	0.4 0.5 0.75	Vdc
Base – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)	V <sub>BE(sat)</sub>	-	0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS	-		•	
Output Capacitance (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	7.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	_	130	pF
Small–Signal Current Gain (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz)	h <sub>fe</sub>	1.0	_	_

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu\text{s},$  Duty Cycle  $\leq$  2.0%.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MPSA44	TO-92	5000 Units / Box
MPSA44G	TO-92 (Pb-Free)	5000 Units / Box
MPSA44RL1	TO-92	2000 / Tape & Reel
MPSA44RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
MPSA44RLRA	TO-92	2000 / Tape & Reel
MPSA44RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

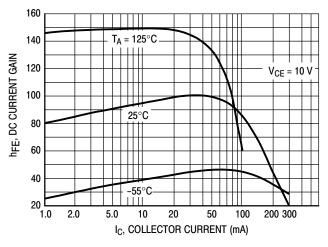


Figure 1. DC Current Gain

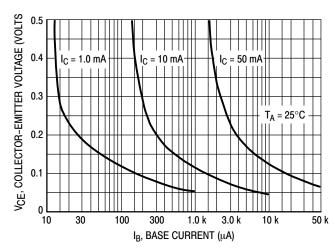


Figure 2. Collector Saturation Region

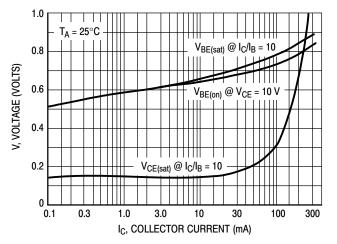


Figure 3. "On" Voltages

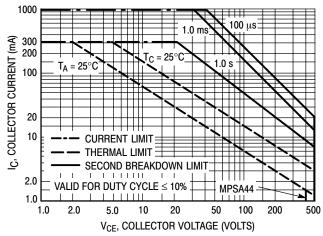


Figure 4. Active Region - Safe Operating Area

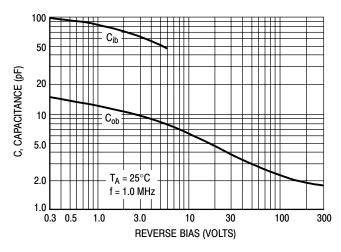


Figure 5. Capacitance

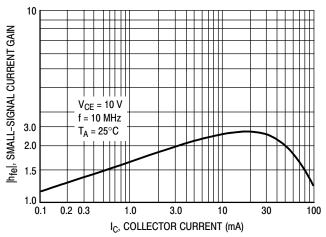


Figure 6. High Frequency Current Gain

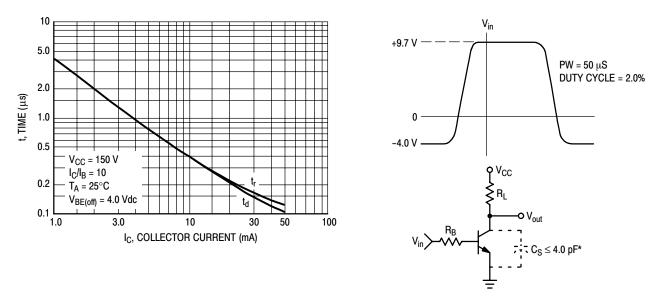


Figure 7. Turn-On Switching Times and Test Circuit

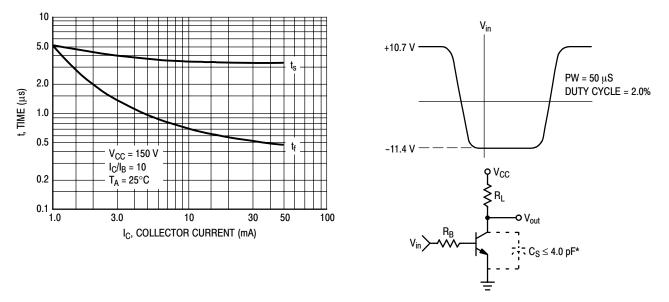
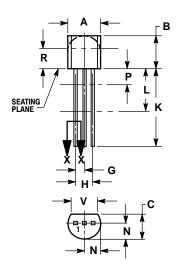


Figure 8. Turn-Off Switching Times and Test Circuit

\*Total Shunt Capacitance or Test Jig and Connectors.

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3 43	

STYLE 1:

PIN 1. EMITTER

2. BASE

3. COLLECTOR

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